



End Term (Even) Semester Examination May-June 2025

Roll no.

Name of the Program and semester:

Name of the Course: CMOS Design

Course Code: TEC 611

Time: 3 hour

Maximum Marks: 100

Note:

- (i) All the questions are compulsory.
- (ii) Answer any two sub questions from a, b and c in each main question.
- (iii) Total marks for each question is 20 (twenty).
- (iv) Each sub-question carries 10 marks.

Q1. (2X10=20 Marks) CO1

- a. Explain the difference between Dry Oxidation and wet Oxidation, and what are the applications of oxidations in VLSI.
- b. Explain the process of creation n-well in MOS.
- c. What is twin tub and Latch up explain in brief.

Q2. (2X10=20 Marks) CO2

- a. Design the stick diagram of $Y = (AB+E+CD)'$
- b. Explain in detail about Lambda (λ) based layout design rules.
- c. Draw the Layout of Boolean expression $Y = (AB+C)'$

Q3. (2X10=20 Marks) CO3

- a. Implement the Boolean expression $Y = \{AB(C+D) + (E+F)G\}'$ using CMOS.
- b. Derive the expression of saturation current in MOS device.
- c. The slope of the I_D vs V_{GS} curve of an n – channel MOSFET in linear region is $10^{-3} \Omega^{-1}$ at $V_{DS}=0.1V$. For the same device, neglecting channel length modulation, find the slope of the $\sqrt{I_D}$ vs V_{GS} curve (in \sqrt{AV}) under saturation region.

Q4. (2X10=20 Marks) CO4

- a. Explain the working principles of the following memory and logic technologies:
 - (i) Anti-fuse
 - (ii) EPROM
 - (iii) SRAM
- b. What are programmable logic cells? Briefly discuss their role in the implementation of complex logic functions.
- c. Define programmable inversion and expander logic in the context of programmable logic arrays or FPGAs. Explain how they contribute to logic optimization.

Q5. (2X10=20 Marks) CO5

- a. Explain the internal architecture and programming technologies of Field Programmable Gate Arrays (FPGAs).
- b. What do you understand by programmable I/O blocks in FPGA?
- c. What are the dedicated specialized components of FPGA, and the applications of FPGA?